

This Response is being submitted to the Examiner's Action dated December 3, 2001, together with a three month time extension to extend the time for response to and including June 3, 2002.

In the Claims:

Amend claims 58 and 59 as follows:

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M  
58. (Amended) A method as claimed in claim 56 wherein the ions are implanted with an energy that produces a doped region in the substrate extending to a predetermined depth and the thermal energy imparted by the ions has a diffusion length, during the duration of the pulse, that is less than one-hundred (100) microns.

59. (Amended) A method as claimed in claim 56 wherein the ions include at least one boron (B), aluminum (Al), gallium (Ga), indium (In), arsenic (As), phosphorus (P), and antimony (Sb).

REMARKS

Claims 58 and 59 were rejected by the Examiner under 35 USC §112 as being indefinite. More specifically, there is no antecedent basis for the term "the ions" in either of claims 58 and 59.

Claims 58 and 59 have been amended to change their dependency to claim 56 from which there is antecedent basis for "the ions".

Claims 1, 7, 14, 16-20, 22-23, 53, 61, 63-66, 69 and 71-72 were rejected by the Examiner as being obvious from Asakawa (JP 06340500). Of those claims, claims 1 and 53 are independent claims and will be addressed first.

Claim 1 calls for "annealing at least one region of a semiconductor substrate with